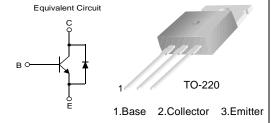


FJP5304D

High Voltage High Speed Power Switch Application

- Wide Safe Operating Area
- Built-in Free Wheeling diode
- Suitable for Electronic Ballast Application
- Small Variance in Storage Time



NPN Triple Diffused Planar Silicon Transistor

Absolute Maximum Ratings T_C=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	700	V
V _{CEO}	Collector-Emitter Voltage	400	V
V_{EBO}	Emitter-Base Voltage	12	V
I _C	Collector Current (DC)	4	Α
I _{CP}	* Collector Current (Pulse)	8	Α
I _B	Base Current (DC)	2	Α
I _{BP}	* Base Current (Pulse)	4	Α
P _C	Collector Dissipation (T _C =25°C)	70	W
T _{STG}	Storage Temperature	- 65 ~ 150	°C

^{*} Pulse Test Pulse Width = 5ms, Duty Cycle ≥ 1.0%

Electrical Characteristics T_C=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV _{CBO}	Collector-Base Breakdown Voltage	$I_{C} = 1 \text{mA}, I_{E} = 0$	700			V
BV _{CEO}	Collector-Emitter Breakdown Voltage	$I_{C} = 5mA, I_{B} = 0$	400			V
BV _{EBO}	Emitter-Base Breakdown Voltage	$I_E = 1 \text{mA}, I_C = 0$	12			V
I _{CES}	Collector Cut-off Current	$V_{CE} = 700V, V_{EB} = 0$			100	mA
I _{CEO}	Collector Cut-off Current	V _{CE} = 400V, IB = 0			250	mA
I _{EBO}	Emitter Cut-off Current	$V_{EB} = 12V, I_{C} = 0$			100	mA
h _{FE}	DC Current Gain	$V_{CE} = 5V, I_{C} = 10mA$ $V_{CE} = 5V, I_{C} = 2A$	10 8		40	
V _{CE} (sat)	Collector-Emitter Saturation Voltage	$I_C = 0.5A, I_B = 0.1A$ $I_C = 1A, I_B = 0.2A$ $I_C = 2.5A, I_B = 0.5A$		0.7 1.0 1.5	V	
V _{BE} (sat)	Base-Emitter Saturation Voltage	$I_C = 0.5A, I_B = 0.1A$ $I_C = 1A, I_B = 0.2A$ $I_C = 2.5A, I_B = 0.5A$		1.1 1.2 1.3	V	
V_f	Internal Diode Forward Voltage Drop	I _F = 2A			2.5	V

$\textbf{Electrical Characteristics} \hspace{0.1cm} \text{(Continued)} \hspace{0.1cm} \textbf{T}_{\text{C}} = 25^{\circ} \textbf{C} \hspace{0.1cm} \text{unless otherwise noted}$

Symbol	Parameter	Test Condition	Min.	TYP.	Max.	Units	
Inductive Lo	Inductive Load Switching (V _{CC} = 200V)						
t _{stg}	Storage Time	$I_C = 2A, I_{B1} = 0.4A$		0.6		μs	
tf	Fall Time	V_{BE} (off) = -5V, L = 200 μ H		0.1			
Resistive Lo	oad Switching (V _{CC} = 250V)						
t _{stg}	Storage Time	$I_C = 2A$, $I_{B1} = I_{B2} = 0.4A$			2.9	μs	
tf	Fall Time	T _P = 30μs		0.2			

^{*} Pulse test: PW≤300μs, Duty cycle≤2%

Thermal Characteristics

Symbol	Parameter	Max.	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case	1.78	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	62.5	°C/W

Typical Characteristics

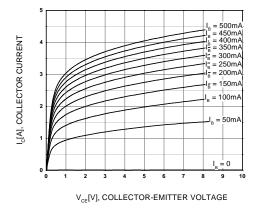


Figure 1. Static Characteristic

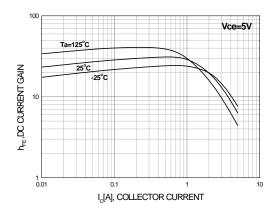


Figure 2. DC Current Gain

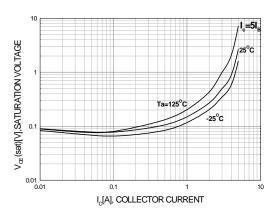


Figure 3. Collector-Emitter Saturation Voltage

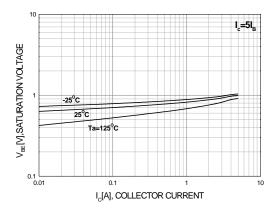


Figure 4. Base-Emitter Saturation Voltage

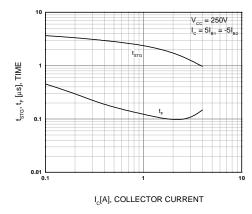


Figure 5. Resitive Load Switching Time

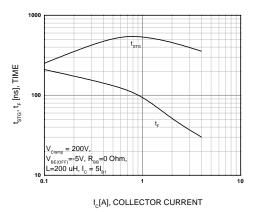


Figure 6. Inductive Load Switching Time

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Typical Characteristics (Continued)

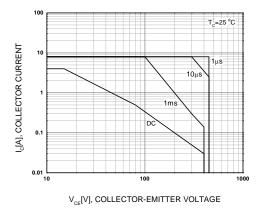


Figure 7. Forward Bias Safe Operating Area

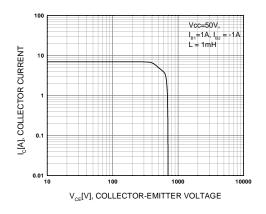


Figure 8. Reverse Bias Safe Operating Area

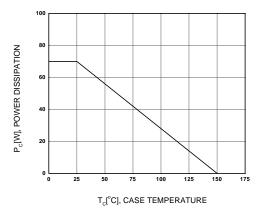
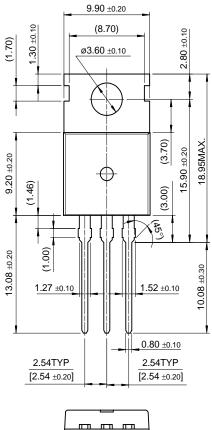


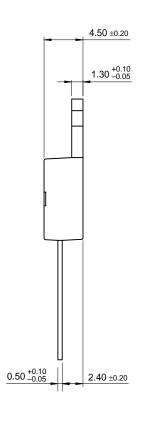
Figure 9. Power Derating

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Package Dimensions

TO-220





10.00 ±0.20

Dimensions in Millimeters

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